

自主封測 品質把控 售後保障

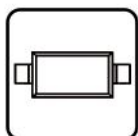
WEB | [WWW.TDSEMIC.COM](http://WWW.TDSEMIC.COM)



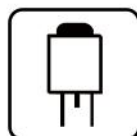
電源管理



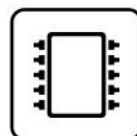
顯示驅動



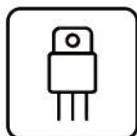
二三極管



LDO穩壓器



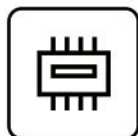
觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

### SS54B-TD

### 產品規格說明書

DO-214AA  
(SMB)



SS52-SS520

## Features:

- ☐ Metal silicon junction, majority carrier conduction
- ☐ For surface mounted applications
- ☐ Low power loss, high efficiency
- ☐ Fast switching for high efficiency
- ☐ High forward surge current capability
- ☐ For use in low voltage, high frequency inverters



1.Cathode 2. Anode

## Absolute Maximum Ratings\* (TA=25°C Unless otherwise noted)

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	SS52	SS54	SS56	SS58	SS510	SS512	SS515	SS520	Units
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V <sub>RMS</sub>	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	I <sub>F(AV)</sub>	5.0								A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I <sub>FSM</sub>	150								A
Max Instantaneous Forward Voltage at 5A	V <sub>F</sub>	0.55	0.70	0.85				0.95	V	
Maximum DC Reverse Current   T <sub>a</sub> = 25°C at Rated DC Reverse Voltage   T <sub>a</sub> = 100°C	I <sub>R</sub>	0.3 10			0.2 5			0.1 2	mA	
Typical Junction Capacitance <sup>(1)</sup>	C <sub>j</sub>	500	300							pF
Typical Thermal Resistance <sup>(2)</sup>	R <sub>θJA</sub>	45								°C/W
Operating Junction Temperature Range	T <sub>j</sub>	-55 ~ +125				-55 ~ +150				°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ +150								°C

(1) Measured at 1 MHz and applied reverse voltage of 4 V.D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

## Typical Characteristics

